

Customer No.: 31561  
Docket No.: 13531-US-PA  
Application No.: 10/711,498

**AMENDMENT**

Please amend the application as indicated hereafter.

**Claims 1-7 (canceled)**

Claim 8 (currently amended) A pixel structure for a liquid crystal display panel, comprising:

a first substrate;

a single-type low temperature polysilicon thin film transistor disposed over the first substrate, the single-type low temperature polysilicon thin film transistor includes:

a source and a drain disposed over the first substrate;

a channel region disposed between the source and the drain;

a gate-insulating layer disposed on the source, the drain and the channel region; and

a gate disposed on the gate-insulating layer over the channel region;

a pixel structure disposed over the first substrate and electrically connected to the single-type low temperature polysilicon thin film transistor;

a storage capacitor disposed over the first substrate, including a top electrode disposed over the first substrate, an insulating layer disposed on the top electrode and a bottom electrode disposed on the insulating layer, wherein one of the terminals of the storage capacitor is electrically connected to the single-type low temperature polysilicon thin film transistor and the storage capacitor is regarded as a symmetrical capacitor related

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to the single-type low temperature polysilicon thin film transistor;

a second substrate disposed over the first substrate;

an electrode film disposed on the second substrate;

a liquid crystal layer disposed between the first substrate and the second substrate; and

a liquid crystal capacitor disposed between the first substrate and the second substrate, wherein one of the terminals of the liquid crystal capacitor and the one of the terminals of the storage capacitor are [[is]] electrically connected to a same terminal of the single-type low temperature polysilicon thin film transistor while the other terminal of the liquid crystal capacitor and the other terminal of the storage capacitor are electrically connected to a common electrode.

wherein the material of the source and the drain is the same as that of the bottom electrode.

Claim 9 (Original) The pixel structure of claim 8, wherein the single-type low temperature polysilicon thin film transistor comprises a P-type low temperature polysilicon thin film transistor.

Claim 10 (Original) The pixel structure of claim 9, wherein the terminals of the storage capacitor comprises a top electrode and a bottom electrode such that the bottom electrode is a P-doped region.

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Claim 11 (Original) The pixel structure of claim 8, wherein the single-type low temperature polysilicon thin film transistor comprises an N-type low temperature polysilicon thin film transistor.

Claim 12 (Original) The pixel structure of claim 11, wherein the terminals of the storage capacitor comprises a top electrode and a bottom electrode such that the bottom electrode is an N-doped region.

Claim 13 (Original) The pixel structure of claim 8, wherein the single-type low temperature polysilicon thin film transistor comprises a single gate low temperature polysilicon thin film transistor or a dual gate low temperature polysilicon thin film transistor.

Claim 14 (Original) The pixel structure of claim 8, wherein the terminals of the liquid crystal capacitor comprises the electrode film and the pixel electrode.

Claim 15 (Original) The pixel structure of claim 8, further comprising a color filter layer disposed between the second substrate and the electrode film.

**Claim 16 (canceled)**